

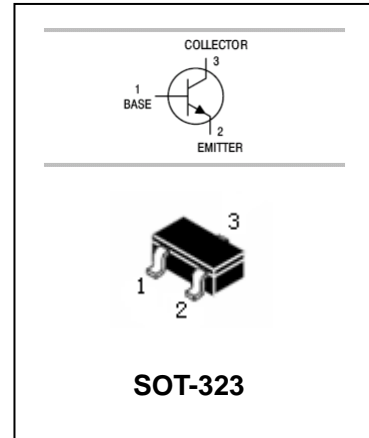


Silicon Epitaxial Planar Transistor

2SC4155

FEATURES

- Small collector to emitter saturation voltage
VCE(sat)=0.3V max
- Excellent linearity of DC forward gain.
- Super mini package for easy mounting



APPLICATIONS

- For Hybrid IC, small type machine low frequency voltage Amplify application.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC4155	HQ/HR/HS/HT	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	6	V
I _O	Collector Current -Continuous	100	mA
P _C	Collector Dissipation	200	mW
T _{stg}	Storage Temperature	-55 to +150	°C
T _j	Junction Temperature	150	°C



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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	50	-	-	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=100\mu A, I_B=0$	50	-	-	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB}=50V, I_E=0$	-	-	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$	-	-	0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6V, I_C=1mA$	120	-	820	
	$h_{FE(2)}$	$V_{CE}=6V, I_C=0.1mA$	70	-	-	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_{CE}=100mA, I_B=10mA$	-	-	0.3	V
Transition frequency	f_T	$V_{CE}=6V, I_C=-10mA$	-	200	-	MHz
Collector output capacitance	C_{ob}	$V_{CB}=6V, I_E=0, f=1MHz$	-	4	-	pF
Noise Figure	NF	$V_{CE}=6V, I_E=-0.1mA, f=1kHz, R_G=2k\Omega$	-	-	15	dB

CLASSIFICATION OF $h_{FE(1)}$

Range	Q	R	S	T
Range	120-270	180-390	270-560	390-820
Marking	HQ	HR	HS	HT



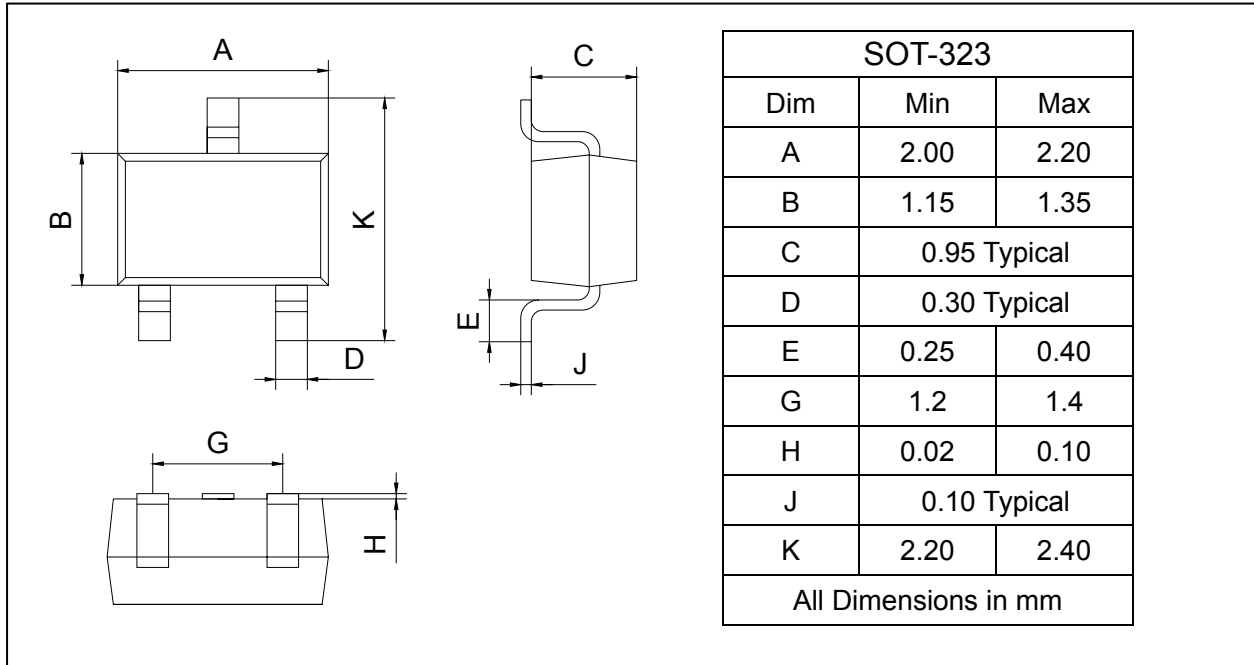
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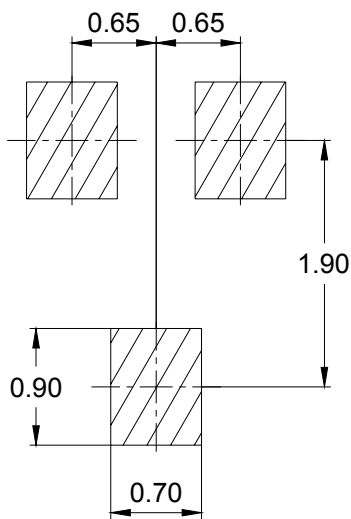
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC4155	SOT-323	3000/Tape&Reel